





N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low Gate Charge
- Low R_{DS(ON)}:
 - 33 m Ω @V_{GS} = 10V
 - 40 m Ω @V_{GS} = 4.5V
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- "Green" Device (Note 4)

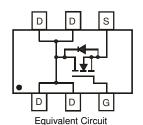
Mechanical Data

- Case: SOT-26
- Case Material Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
 - Weight: 0.008 grams (approximate)

SOT-26



TOP VIEW



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	30	V	
Gate-Source Voltage		V_{GSS}	±20	V	
Drain Current (Note 1) Continuous	$T_A = 25$ °C $T_A = 70$ °C	I _D	6.9 5.8	Α	
Pulsed Drain Current (Note 2)		I _{DM}	20	Α	
Body-Diode Continuous Current (Note 1)		Is	2.25	Α	

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	P_D	2	W
Thermal Resistance, Junction to Ambient (Note 1) t ≤10s	$R_{ hetaJA}$	62.5	°C /W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width t \leq 10s.
- 2. Repetitive Rating, pulse width limited by junction temperature.
- 3. No purposefully added lead.
- 4. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

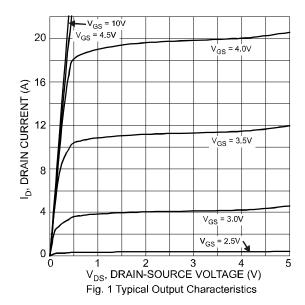


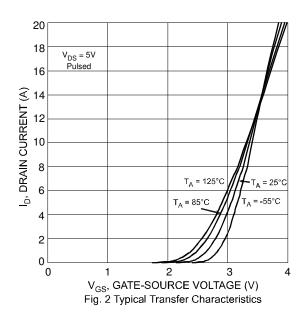
Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
STATIC CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	30			V	$I_D = 250 \mu A, V_{GS} = 0 V$
	= 25°C = 55°C	I _{DSS}	_	_	1 5	μΑ	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Body Leakage Current		I _{GSS}			±100	nA	$V_{DS} = 0V, V_{GS} = \pm 20V$
Gate Threshold Voltage		V _{GS(th)}	1.0		2.1	٧	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance (Note 5)		R _{DS (ON)}		25 36	33 40	mΩ	$V_{GS} = 10V, I_D = 6.9A$ $V_{GS} = 4.5V, I_D = 5.0A$
Forward Transconductance (Note 5)		9 FS		5		S	$V_{DS} = 10V, I_D = 8A$
Diode Forward Voltage (Note 5)		V_{SD}		0.7	1.1	٧	$I_S = 2.25A, V_{GS} = 0V$
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance		Ciss	_	755	_	pF	V 10V V 0V
Output Capacitance		Coss		136		pF	$V_{DS} = 10V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance		Crss		108		pF	1 = 1.0MHZ
Gate Resisitance		Rg		0.89		Ω	$V_{GS} = 0V$, $V_{DS} = 0V$, $f = 1MHz$
SWITCHING CHARACTERISTICS		•					
Total Gate Charge		Qg	_	6.4 13.0	_	nC	$V_{GS} = 4.5V, V_{DS} = 15V, I_D = 5A$ $V_{GS} = 10V, V_{DS} = 15V, I_D = 6.9A$
Gate-Source Charge		Q_{gs}		1.9		nC	$V_{GS} = 10V, V_{DS} = 15V, I_D = 6.9A$
Gate-Drain Charge		Q_{gd}		3.2		nC	$V_{GS} = 10V, V_{DS} = 15V, I_D = 6.9A$
Turn-On Delay Time		t _{D(on)}		11		ns	
Turn-On Rise Time		t _r	_	7	_	ns	$V_{DD} = 15V, V_{GS} = 10V,$
Turn-Off Delay Time		t _{D(off)}	_	63	_	ns	$R_D = 1.8\Omega$, $R_G = 6\Omega$
Turn-Off Fall Time		t _f	_	30	_	ns	

Notes:

- 5. Test pulse width t = 300ms.6. Guaranteed by design. Not subject to production testing.







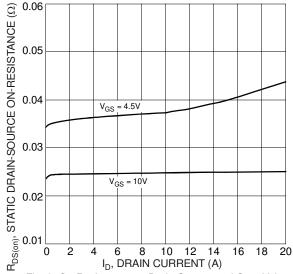


Fig. 3 On-Resistance vs. Drain Current and Gate Voltage

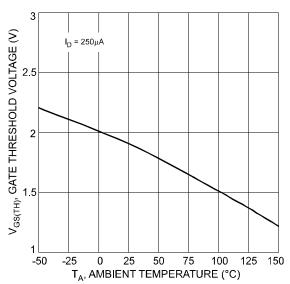


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature

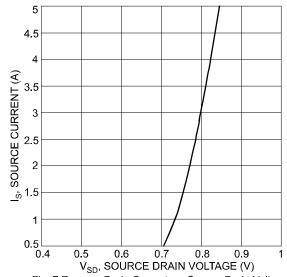
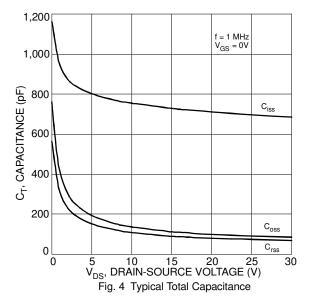


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage



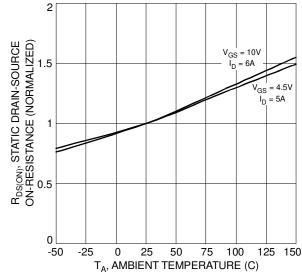


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

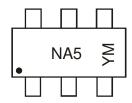


Ordering Information (Note 7)

Part Number	Case	Packaging
DMN3033LDM-7	SOT-26	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

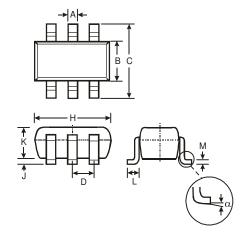


NA5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: U = 2007) M = Month (ex: 9 = September)

Date Code Key

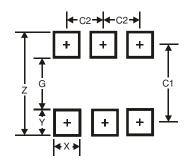
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Year	2007	20	08	2009	2010	20)11	2012	2013	20)14	2015
Code	U	\	/	W	Х	,	Y	Z	Α		В	С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Package Outline Dimensions



SOT-26						
Dim	Min	Max	Тур			
Α	0.35	0.50	0.38			
В	1.50	1.70	1.60			
O	2.70	3.00	2.80			
D	_	0.95				
Н	2.90	3.10	3.00			
7	0.013	0.10	0.05			
K	1.00	1.30	1.10			
L	0.35	0.55	0.40			
М	0.10	0.20	0.15			
α	0°	8°	_			
All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Υ	0.80
C1	2.40
C2	0.95



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